



DMMT5401

MATCHED PNP SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

Epitaxial Planar Die Construction

Complementary NPN Type Available (DMMT5551) Ideal for Low Power Amplification and Switching

Intrinsically Matched PNP Pair (Note 1)

2% Matched Tolerance, hFE, VCE(SAT), VBE(SAT)

Lead Free/RoHS Compliant (Note 4)

"Green" Device, Note 5 and 6

Mechanical Data

Case: SOT-26

Case Material: Molded Plastic, "Green" Molding Compound, Note 7. UL Flammability Classification

Rating 94V-0

Moisture Sensitivity: Level 1 per J-STD-020C

Terminal Connections: See Diagram

Terminals: Solderable per MIL-STD-202, Method 208

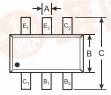
Lead Free Plating (Matte Tin Finish annealed over

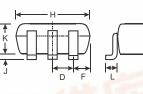
Copper leadframe).

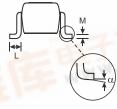
Marking (See Page 2): K4S

Order & Date Code Information: See Page 2

Weight: 0.006 grams (approximate)







SOT-26										
Dim	Min	Max	Тур							
Α	0.35	0.50	0.38							
В	1.50	1.70	1.60							
С	2.70	3.00	2.80							
D			0.95							
F			0.55							
Н	2.90	3.10	3.00							
J	0.013	0.10	0.05							
K	1.00	1.30	1.10							
L	0.35	0.55	0.40							
M	0.10	0.20	0.15							
0 8										
All Dimensions in mm										



Maximum Ratings @ T_A = 25 C unless otherwise specified

Characteristic	Symbol	Value	Unit		
Collector-Base Voltage	V _{CBO}	-160	V		
Collector-Emitter Voltage	V _{CEO}	-150	V		
Emitter-Base Voltage	V _{EBO}	-5.0	V		
Collector Current - Continuous (Note 2)	I _C	-200	mA		
Power Dissipation (Note 2, 3)	P _d	300	mW		
Thermal Resistance, Junction to Ambient (Note 2)	R JA	417	°C/W		
Operating and Storage and Temperature Range	T _j , T _{STG}	-55 to +150	GOC		

Notes:

- 1. Built with adjacent die from a single wafer.
- 2. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- Maximum combined dissipation.
- 4. No purposefully added lead.
- 5. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- 6. Product manufactured with Date Code 0627 (week 27, 2006) and newer are built with Green Molding Compound. Product manufactured prior to Date Code 0627 are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.





Electrical Characteristics @ TA = 25 C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition				
OFF CHARACTERISTICS (Note 7)									
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-160		V	I _C = -100 A, I _E = 0				
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-150		V	$I_C = -1.0 \text{mA}, I_B = 0$				
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5.0		V	$I_E = -10 A, I_C = 0$				
Collector Cutoff Current	I _{CBO}		-50	nA A	$V_{CB} = -120V, I_{E} = 0$ $V_{CB} = -120V, I_{E} = 0, T_{A} = 100 C$				
Emitter Cutoff Current	I _{EBO}		-50	nA	$V_{EB} = -3.0V, I_{C} = 0$				
ON CHARACTERISTICS (Note 7)	ON CHARACTERISTICS (Note 7)								
DC Current Gain (Note 8)	h _{FE}	50 60 50	240		I _C = -1.0mA, V _{CE} = -5.0V I _C = -10mA, V _{CE} = -5.0V I _C = -50mA, V _{CE} = -5.0V				
Collector-Emitter Saturation Voltage	V _{CE} (SAT)		-0.2 -0.5	V	I _C = -10mA, I _B = -1.0mA I _C = -50mA, I _B = -5.0mA				
Base-Emitter Saturation Voltage	V _{BE(SAT)}		-1.0	V	I _C = -10mA, I _B = -1.0mA I _C = -50mA, I _B = -5.0mA				
SMALL SIGNAL CHARACTERISTICS									
Output Capacitance	Cobo		6.0	pF	$V_{CB} = -10V$, $f = 1.0MHz$, $I_E = 0$				
Small Signal Current Gain	h _{fe}	40	200		$V_{CE} = -10V, I_{C} = -1.0mA,$ f = 1.0kHz				
Current Gain-Bandwidth Product	f⊤	100	300	MHz	$V_{CE} = -10V, I_{C} = -10mA,$ f = 100MHz				
Noise Figure	NF		8.0	dB	V _{CE} = -5.0V, I _C = -200 A, R _S = 10 f = 1.0kHz				

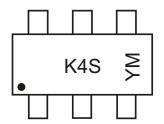
Ordering Information (Note 6 & 9)

Device	Packaging	Shipping			
DMMT5401-7-F	SOT-26	3000/Tape & Reel			

Notes:

- 6. Product manufactured with Date Code 0627 (week 27, 2006) and newer are built with Green Molding Compound. Product manufactured prior to Date Code 0627 are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. The DC Current Gain, h_{FE}, (matched at I_C = -10mA and V_{CE} = -5V) Collector Emitter Saturation Voltage, $V_{CE(SAT)}$, and Base Emitter Saturation Voltage, $V_{BE(SAT)}$ are matched with typical matched tolerances of 1% and maximum of 2%.
- 9. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



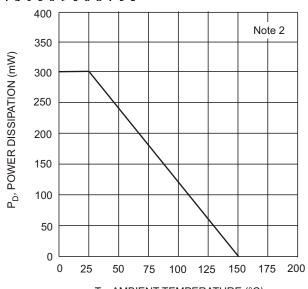
K4S = Product Type Marking Code YM = Date Code Marking Y = Year ex: T = 2006 M = Month ex: 9 = September

Date Code Key

Year	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	R	S	Т	U	V	W	Х	Υ	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

DIODES



T_A, AMBIENT TEMPERATURE (°C) Fig. 1, Max Power Dissipation vs Ambient Temperature

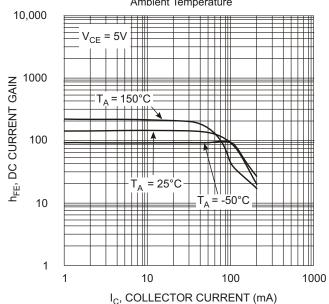
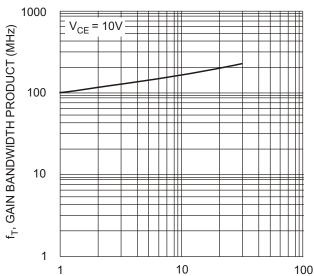


Fig. 3, DC Current Gain vs. Collector Current



 $\rm I_{C},$ COLLECTOR CURRENT (mA) Fig. 5, Gain Bandwidth Product vs Collector Current

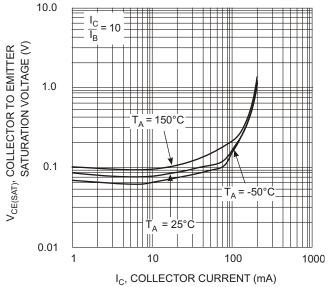
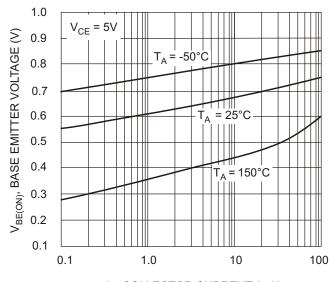


Fig. 2, Collector Emitter Saturation Voltage vs. Collector Current



I_C, COLLECTOR CURRENT (mA)
Fig. 4, Base Emitter Voltage vs. Collector Current



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